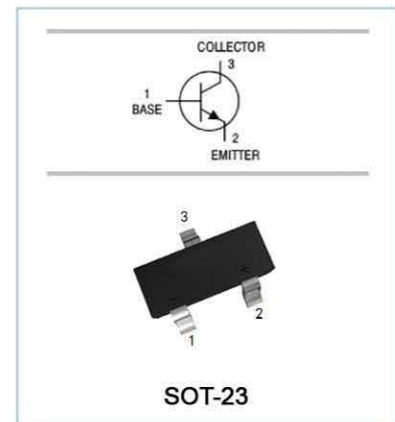


FEATURES

- High current gain bandwidth product.
- power dissipation.($P_C=200\text{mW}$)

APPLICATIONS

- NPN epitaxial silicon transistor.



MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	18	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	200	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^\circ\text{C}$

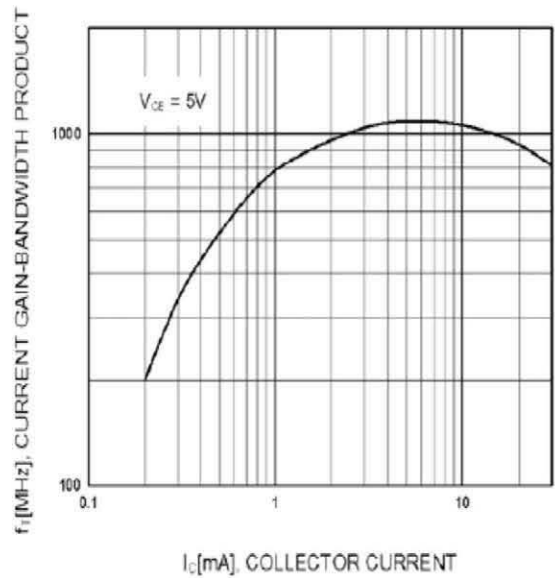
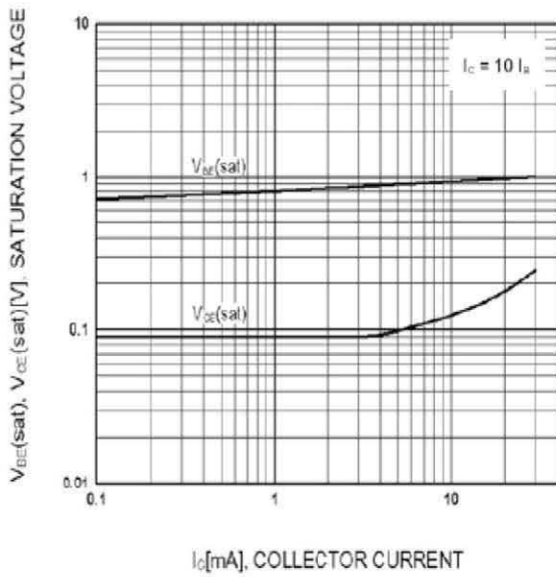
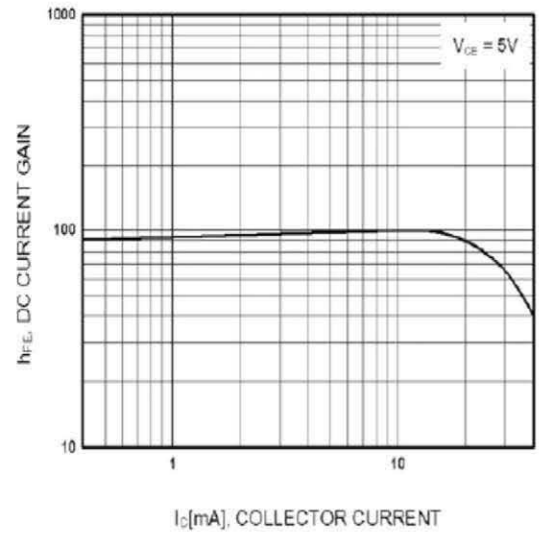
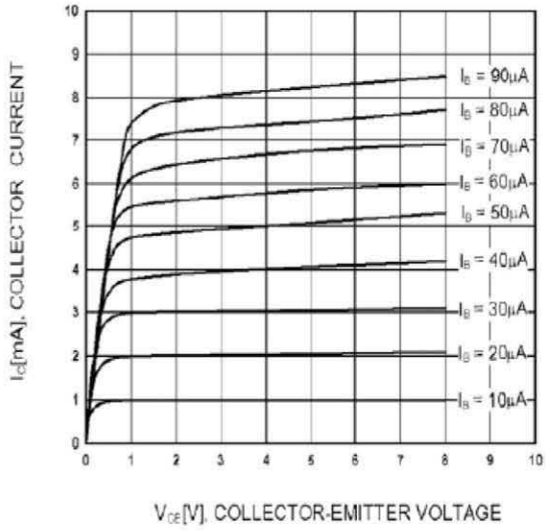
ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=15\text{V}, I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{mA}$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1.4	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=5\text{mA}$ $f=400\text{MHz}$	600			MHz

h_{FE}

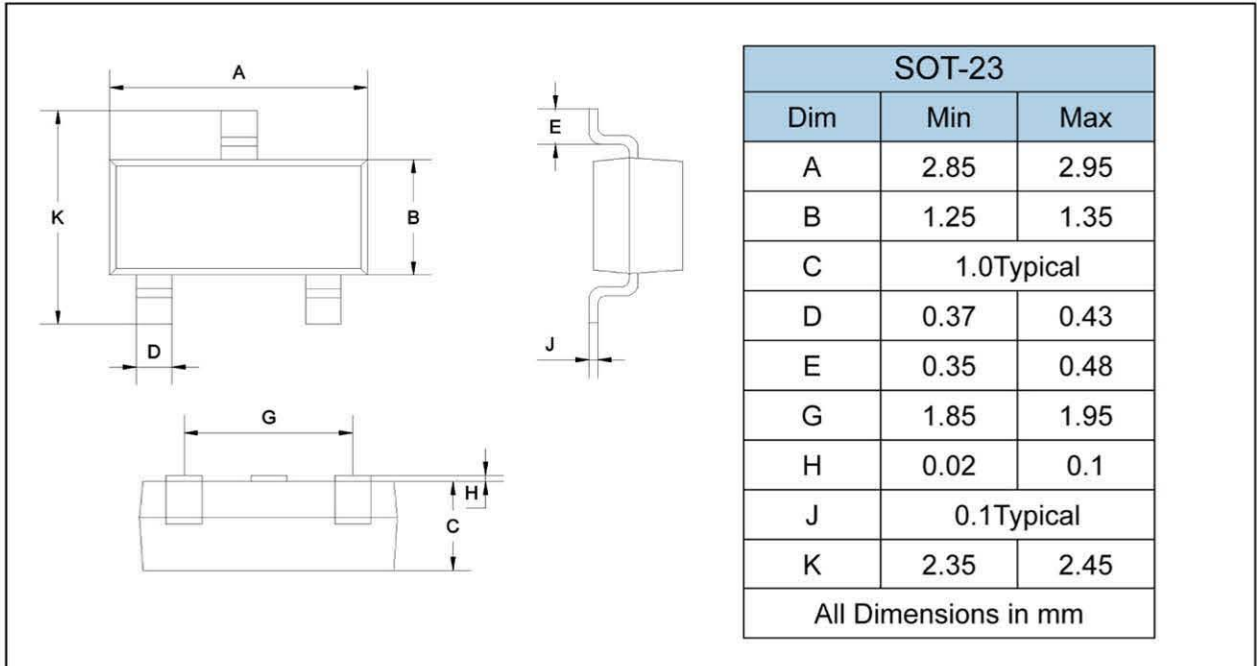
*	R	O	Y
h_{FE}	40~80	70~140	100~200

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



PACKAGE OUTLINE

Plastic surface mounted package



SOLDERING FOOTPRINT

